

N-Channel 650V (D-S) Power MOSFET

PRODUCT SUMMARY		
V _{DS} (V) at T _J max.	650	
R _{DS(on)} max. at 25 °C (Ω)	V _{GS} = 10 V	0.82
Q _g max. (nC)	57	
Q _{gs} (nC)	4.0	
Q _{gd} (nC)	5.4	
Configuration	Single	

FEATURES

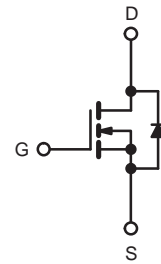
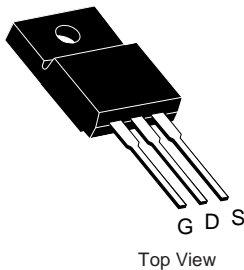
- Low figure-of-merit (FOM) R_{on} × Q_g
- Low input capacitance (C_{iss})
- Reduced switching and conduction losses
- Ultra low gate charge (Q_g)
- Avalanche energy rated (UIS)



APPLICATIONS

- Server and telecom power supplies
- Switch mode power supplies (SMPS)
- Power factor correction power supplies (PFC)
- Lighting
 - High-intensity discharge (HID)
 - Fluorescent ballast lighting
- Industrial

TO-220 FULLPAK



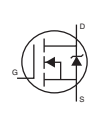
N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)				
PARAMETER	SYMBOL		LIMIT	UNIT
Drain-Source Voltage	V _{DS}		650	V
Gate-Source Voltage	V _{GS}		± 30	
Continuous Drain Current (T _J = 150 °C)	V _{GS} at 10 V	T _C = 25 °C	10	A
		T _C = 100 °C	8	
Pulsed Drain Current ^a	I _{DM}		35	
Linear Derating Factor			1.67/1.5/0.3	W/°C
Single Pulse Avalanche Energy ^b	E _{AS}		86	mJ
Maximum Power Dissipation	P _D		178/156/53	W
Operating Junction and Storage Temperature Range	T _J , T _{stg}		-55 to +150	°C
Drain-Source Voltage Slope	T _J = 125 °C		50	V/ns
Reverse Diode dV/dt ^d			4.5	
Soldering Recommendations (Peak Temperature) ^c	for 10 s		300	°C

Notes

- Repetitive rating; pulse width limited by maximum junction temperature.
- V_{DD} = 50 V, starting T_J = 25 °C, L = 28.2 mH, R_g = 25 Ω, I_{AS} = 3.5 A.
- 1.6 mm from case.
- I_{SD} ≤ I_D, dI/dt = 100 A/μs, starting T_J = 25 °C.

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	R_{thJA}	-	63	°C/W
Maximum Junction-to-Case (Drain)	R_{thJC}	-	0.6	

SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$		650	-	-	V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^\circ\text{C}, I_D = 1\text{ mA}$		-	0.65	-	V/°C
Gate-Source Threshold Voltage (N)	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$		2	-	4	V
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 20\text{ V}$		-	-	± 100	nA
		$V_{GS} = \pm 30\text{ V}$		-	-	± 1	μA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 650\text{ V}, V_{GS} = 0\text{ V}$		-	-	1	μA
		$V_{DS} = 520\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$		-	-	10	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$	$I_D = 4\text{ A}$	-	0.82	-	Ω
Forward Transconductance	g_{fs}	$V_{DS} = 30\text{ V}, I_D = 4\text{ A}$		-	16	-	S
Dynamic							
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = 100\text{ V}, f = 1\text{ MHz}$		-	1900	-	pF
Output Capacitance	C_{oss}			-	400	-	
Reverse Transfer Capacitance	C_{rss}			-	240	-	
Effective Output Capacitance, Energy Related ^a	$C_{o(er)}$	$V_{DS} = 0\text{ V to } 520\text{ V}, V_{GS} = 0\text{ V}$		-	45	-	
Effective Output Capacitance, Time Related ^b	$C_{o(tr)}$			-	62	-	
Total Gate Charge	Q_g	$V_{GS} = 10\text{ V}$	$I_D = 4\text{ A}, V_{DS} = 520\text{ V}$	-	40	57	nC
Gate-Source Charge	Q_{gs}			-	4.0	-	
Gate-Drain Charge	Q_{gd}			-	5.4	-	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 520\text{ V}, I_D = 4\text{ A}, V_{GS} = 10\text{ V}, R_g = 9.1\text{ }\Omega$		-	25	-	ns
Rise Time	t_r			-	55	-	
Turn-Off Delay Time	$t_{d(off)}$			-	70	-	
Fall Time	t_f			-	40	-	
Gate Input Resistance	R_g	$f = 1\text{ MHz}, \text{ open drain}$		-	3.5	-	Ω
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I_S	MOSFET symbol showing the integral reverse p - n junction diode 		-	-	7	A
Pulsed Diode Forward Current	I_{SM}			-	-	18	
Diode Forward Voltage	V_{SD}	$T_J = 25\text{ }^\circ\text{C}, I_S = 4\text{ A}, V_{GS} = 0\text{ V}$		-	-	1.5	V
Reverse Recovery Time	t_{rr}	$T_J = 25\text{ }^\circ\text{C}, I_F = I_S = 4\text{ A}, dI/dt = 100\text{ A}/\mu\text{s}, V_R = 400\text{ V}$		-	190	-	ns
Reverse Recovery Charge	Q_{rr}			-	2.3	-	μC
Reverse Recovery Current	I_{RRM}			-	10	-	A

Notes

- a. $C_{oss(er)}$ is a fixed capacitance that gives the same energy as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DSS} .
- b. $C_{oss(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DSS} .

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Fig. 1 - Typical Output Characteristics

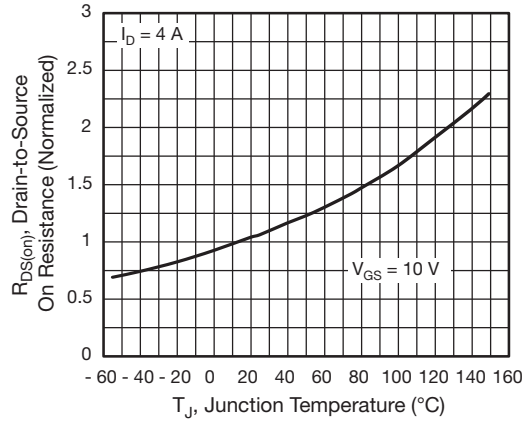


Fig. 4 - Normalized On-Resistance vs. Temperature



Fig. 2 - Typical Output Characteristics



Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage



Fig. 3 - Typical Transfer Characteristics



Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage



Fig. 7 - Typical Source-Drain Diode Forward Voltage



Fig. 9 - Maximum Drain Current vs. Case Temperature



Fig. 8 - Maximum Safe Operating Area

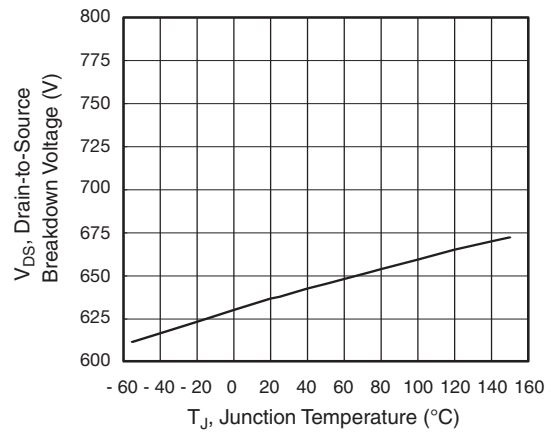


Fig. 10 - Temperature vs. Drain-to-Source Voltage



Fig. 11 - Normalized Thermal Transient Impedance, Junction-to-Case

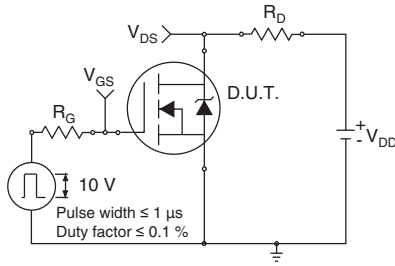


Fig. 12 - Switching Time Test Circuit



Fig. 16 - Basic Gate Charge Waveform



Fig. 13 - Switching Time Waveforms

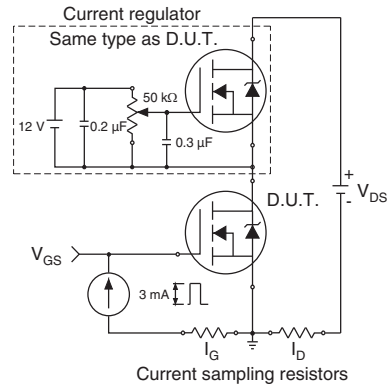


Fig. 17 - Gate Charge Test Circuit



Fig. 14 - Unclamped Inductive Test Circuit



Fig. 15 - Unclamped Inductive Waveforms

Peak Diode Recovery dV/dt Test Circuit

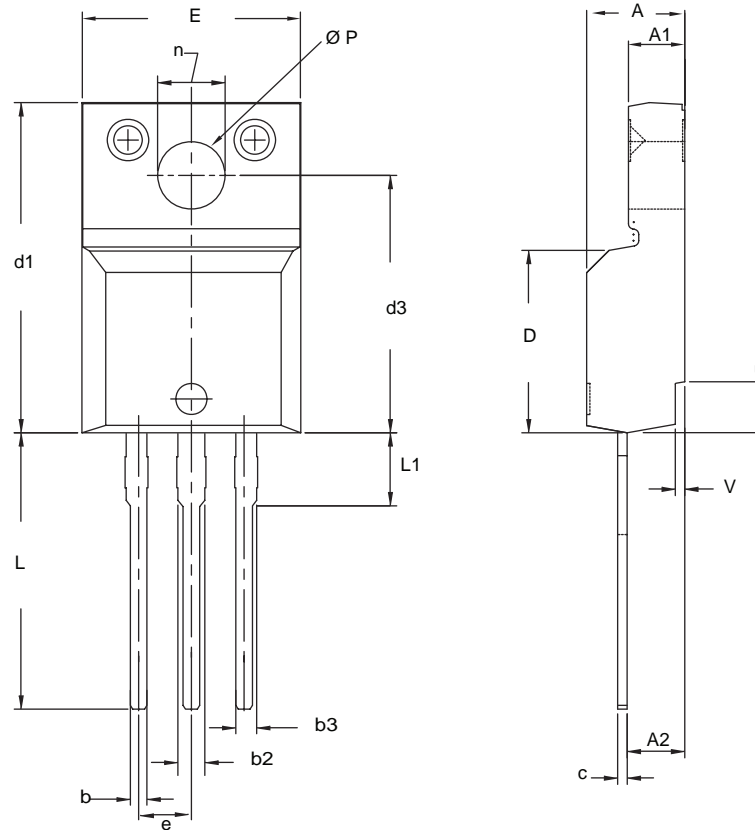


Note

a. $V_{GS} = 5 V$ for logic level devices

Fig. 18 - For N-Channel

TO-220 FULLPAK (HIGH VOLTAGE)



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.570	4.830	0.180	0.190
A1	2.570	2.830	0.101	0.111
A2	2.510	2.850	0.099	0.112
b	0.622	0.890	0.024	0.035
b2	1.229	1.400	0.048	0.055
b3	1.229	1.400	0.048	0.055
c	0.440	0.629	0.017	0.025
D	8.650	9.800	0.341	0.386
d1	15.88	16.120	0.622	0.635
d3	12.300	12.920	0.484	0.509
E	10.360	10.630	0.408	0.419
e	2.54 BSC		0.100 BSC	
L	13.200	13.730	0.520	0.541
L1	3.100	3.500	0.122	0.138
n	6.050	6.150	0.238	0.242
Ø P	3.050	3.450	0.120	0.136
u	2.400	2.500	0.094	0.098
v	0.400	0.500	0.016	0.020

ECN: X09-0126-Rev. B, 26-Oct-09
DWG: 5972

Notes

1. To be used only for process drawing.
2. These dimensions apply to all TO-220, FULLPAK leadframe versions 3 leads.
3. All critical dimensions should C meet $C_{pk} > 1.33$.
4. All dimensions include burrs and plating thickness.
5. No chipping or package damage.

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